



UT3401

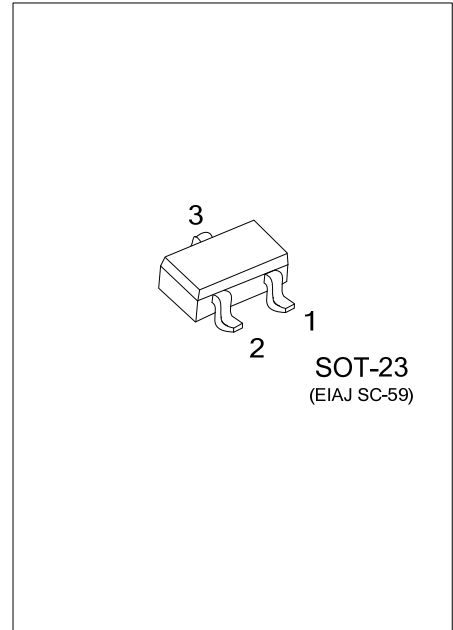
Power MOSFET

P-CHANNEL ENHANCEMENT MODE

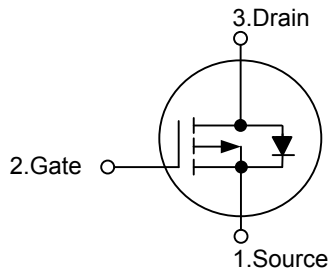
DESCRIPTION

The UTC **UT3401** is P-channel enhancement mode Power MOSFET, designed with high density cell, with fast switching speed, low on-resistance, excellent thermal and electrical capabilities and operation with low gate voltages.

This device is suitable for use as a load switch or in PWM applications.



SYMBOL



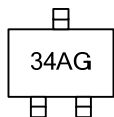
ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			Packing
		1	2	3	
UT3401G-AE3-R	SOT-23	S	G	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>UT3401G-AE3-R</p> <p>(1) Packing Type (2) Package Type (3) Green Package</p>	<p>(1) R: Tape Reel (2) AE3: SOT-23 (3) G: Halogen Free and Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	-30	V
Gate-Source Voltage	V_{GSS}	± 12	V
Continuous Drain Current (Note 1)	I_D	-4.2	A
Pulsed Drain Current (Note 2)	I_{DM}	-30	A
Power Dissipation (Note 1)	P_D	1.4	W
Junction Temperature	T_J	+150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

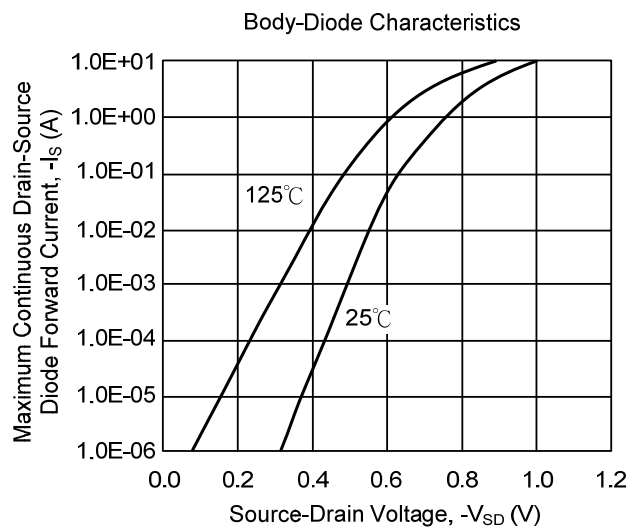
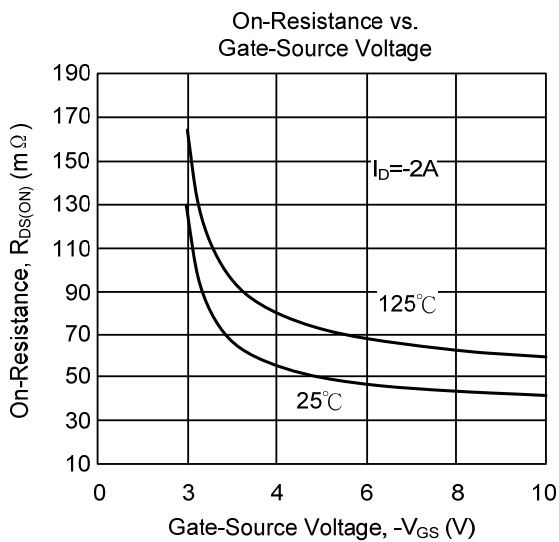
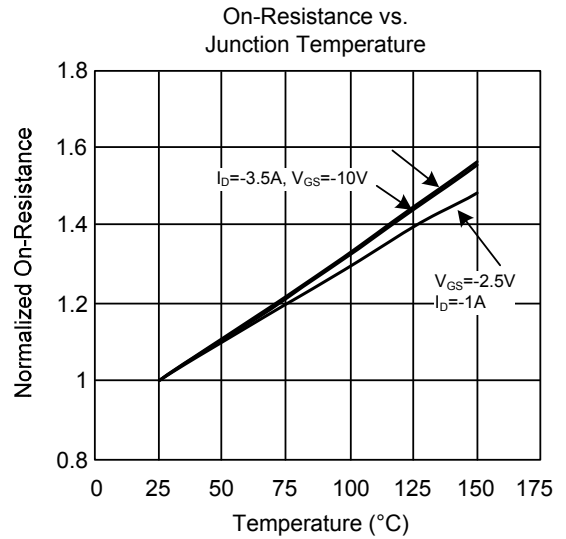
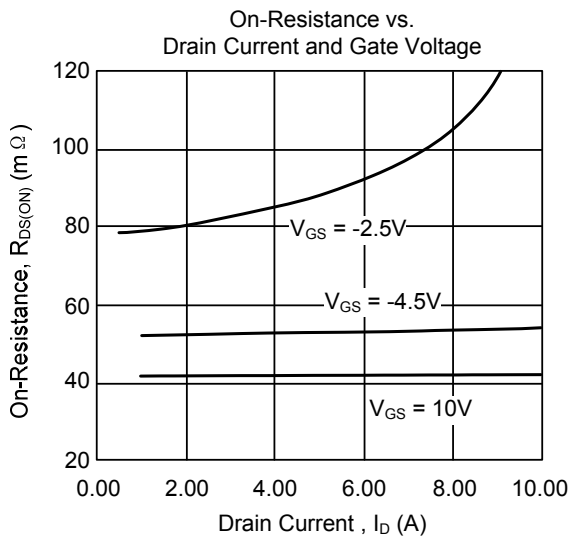
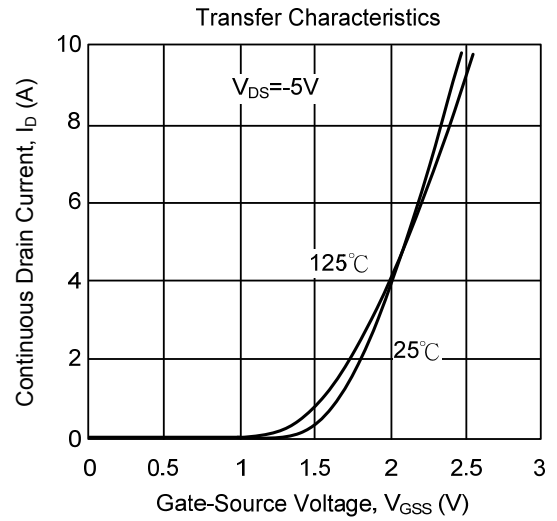
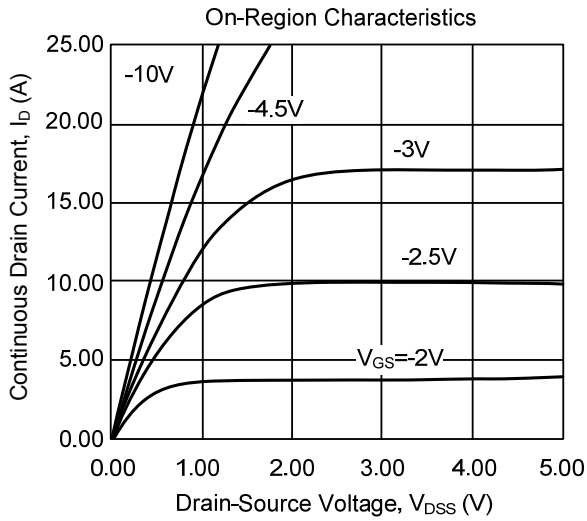
PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Junction-to-Ambient	θ_{JA}		65	90	$^{\circ}\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

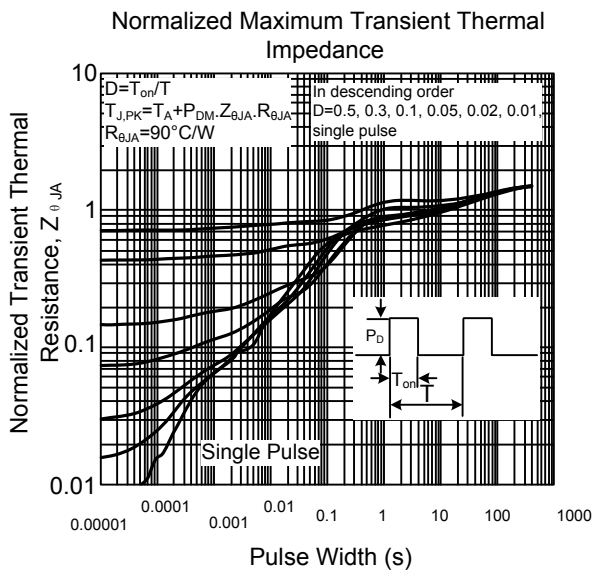
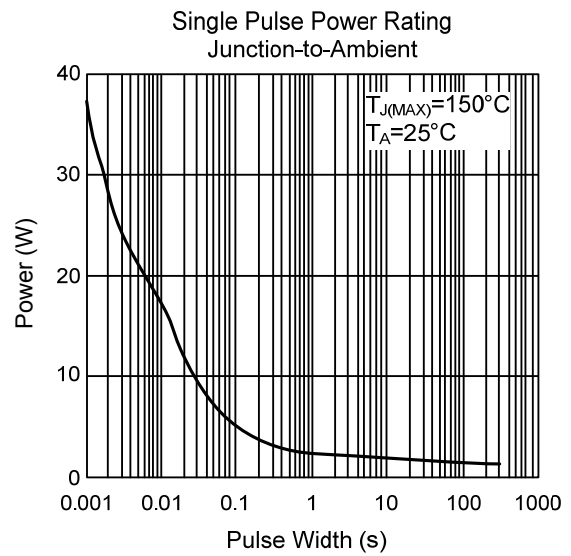
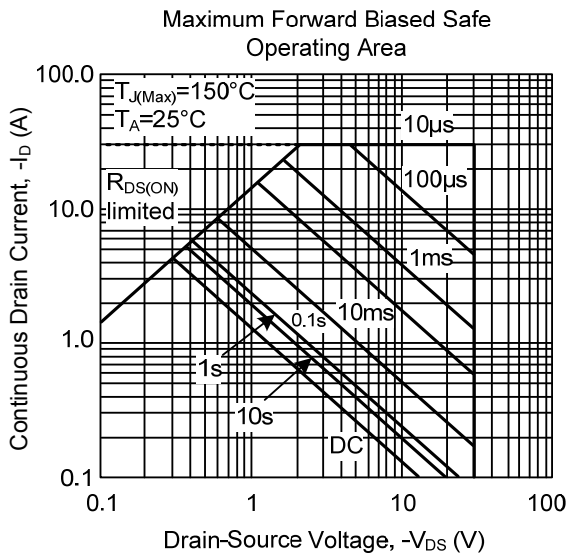
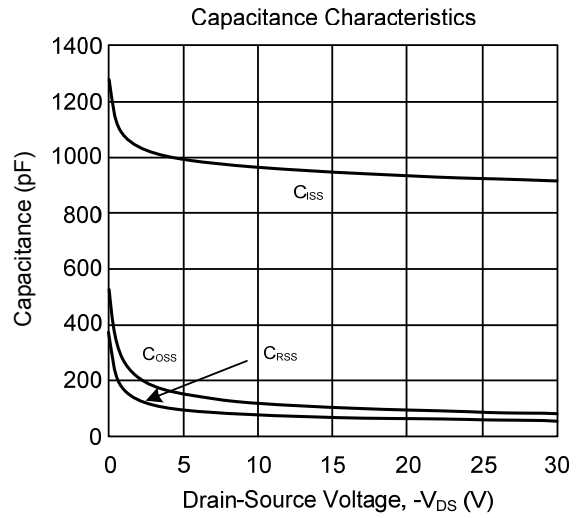
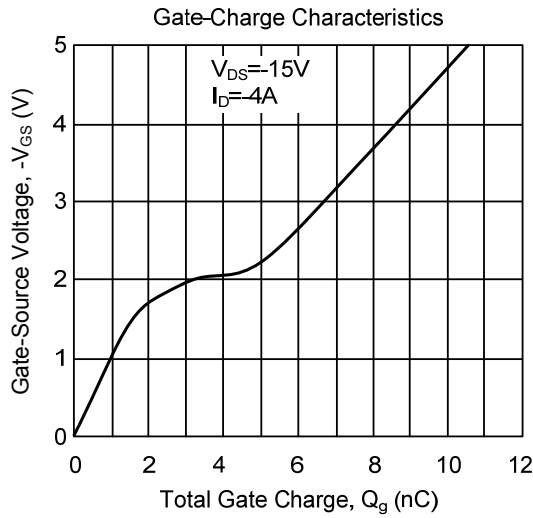
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=-250\mu\text{A}, V_{GS}=0\text{V}$	-30			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=-24\text{V}, V_{GS}=0\text{V}$			-1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm 12\text{V}$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-0.7	-1	-1.3	V
Drain-Source On-State Resistance (Note 2)	$R_{DS(ON)}$	$V_{GS}=-10\text{V}, I_D=-4.2\text{A}$		42	50	m Ω
		$V_{GS}=-4.5\text{V}, I_D=-4\text{A}$		53	65	m Ω
		$V_{GS}=-2.5\text{V}, I_D=-1\text{A}$		80	120	m Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}, V_{DS}=-15\text{V}, f=1\text{MHz}$		954		pF
Output Capacitance	C_{OSS}			115		pF
Reverse Transfer Capacitance	C_{RSS}			77		pF
SWITCHING PARAMETERS						
Turn-ON Delay Time (Note 2)	$t_{D(ON)}$	$V_{GS}=-10\text{V}, V_{DS}=-15\text{V}$ $R_L=3.6\Omega, R_G=6\Omega$		6.3		ns
Turn-ON Rise Time	t_R			3.2		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			38.2		ns
Turn-OFF Fall Time	t_F			12		ns
Total Gate Charge (Note 2)	Q_G	$V_{GS}=-4.5\text{V}, V_{DS}=-15\text{V}, I_D=-4\text{A}$		9.4		nC
Gate-Source Charge	Q_{GS}			2		nC
Gate-Drain Charge	Q_{GD}			3		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage(Note2)	V_{SD}	$V_{DS}=0\text{V}, I_S=-1\text{A}$		-0.75	-1	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				-2.2	A
Reverse Recovery Time	t_{RR}	$I_F=-4\text{A}, dI/dt=100\text{A}/\mu\text{s}$		20.2		ns
Reverse Recovery Charge	Q_{RR}				11.2	

- Notes: 1. Pulse width limited by $T_{J(MAX)}$
 2. Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
 3. Surface mounted on 1 in² copper pad of FR4 board

■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS(Cont.)



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